

FIG. 2b

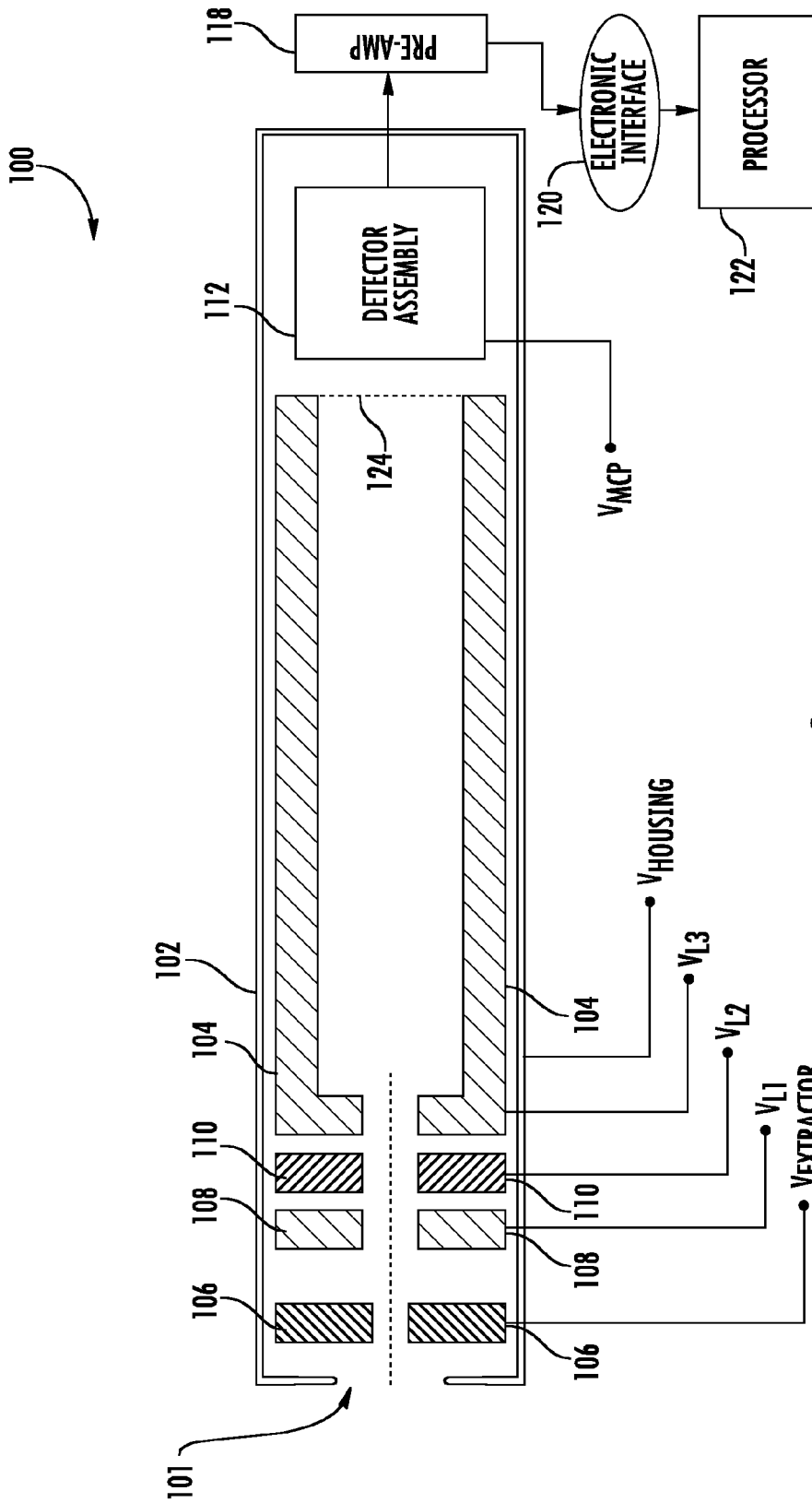


FIG. 3

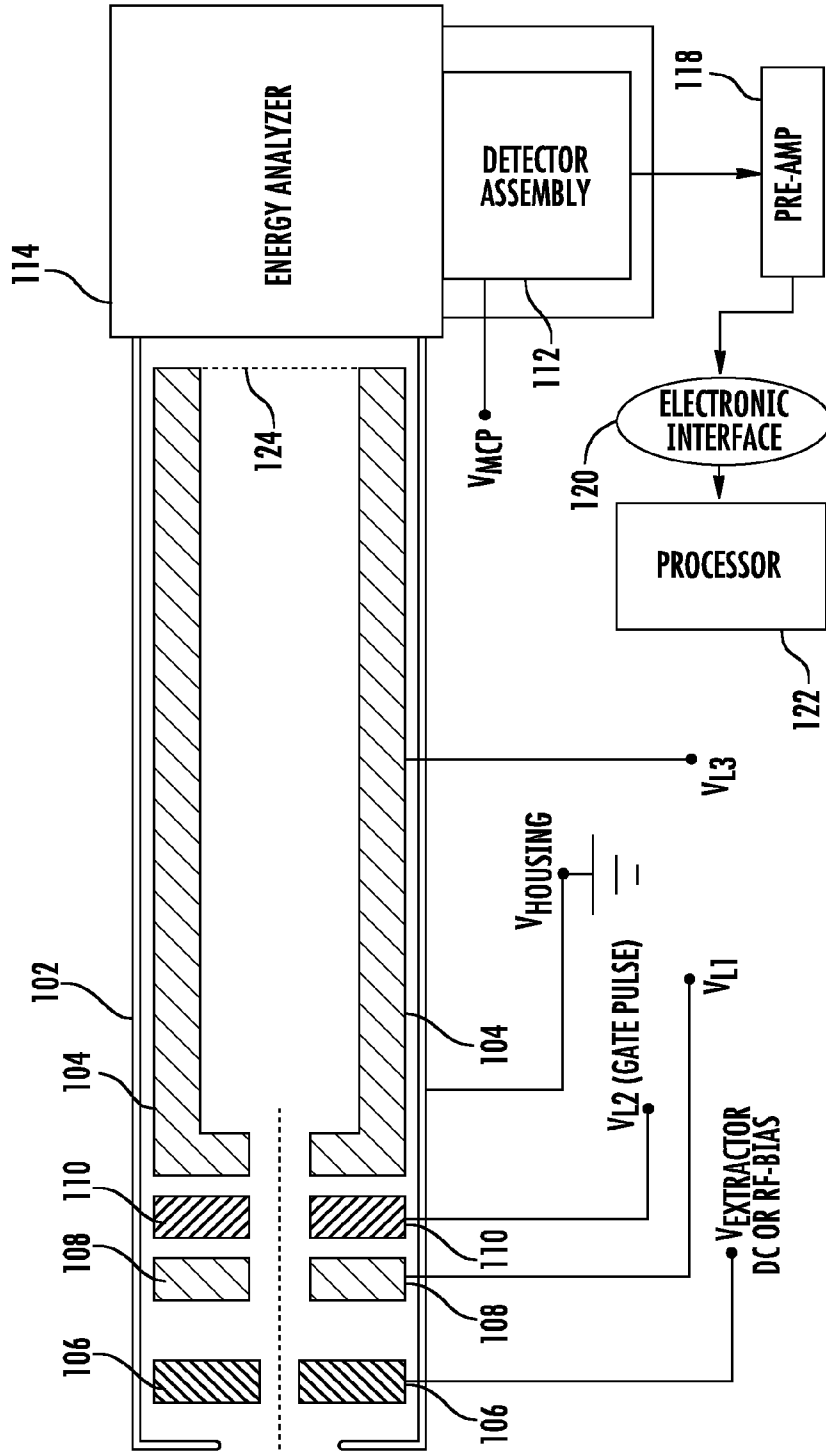


FIG. 4

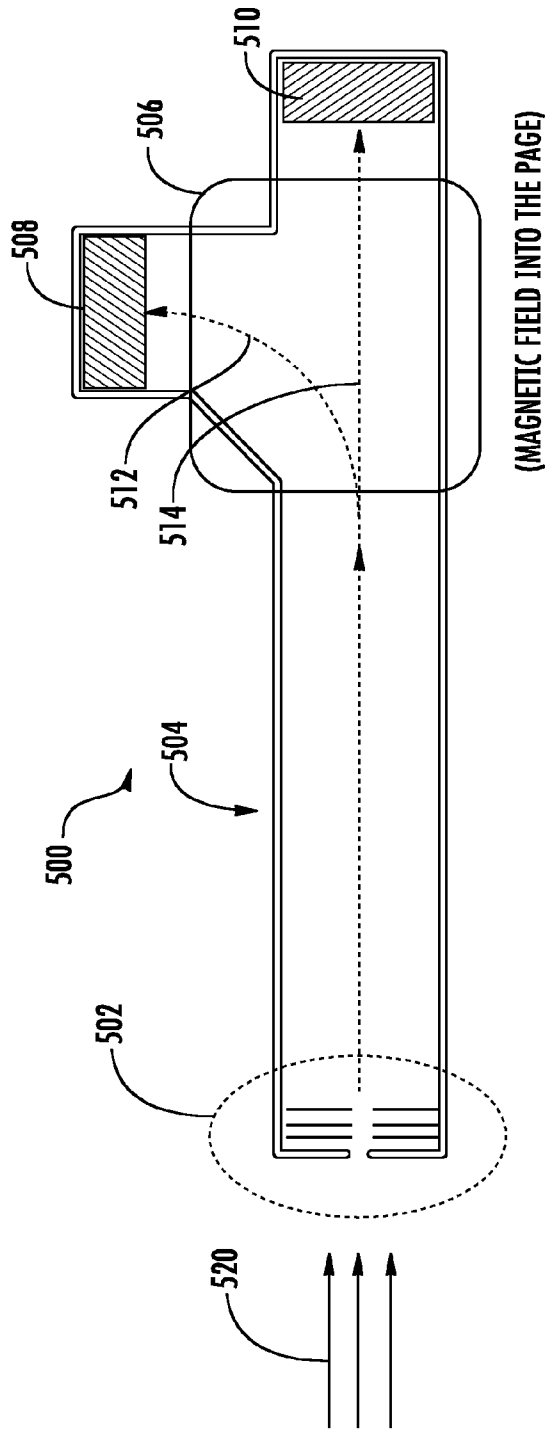


FIG. 5

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TECHNIQUE AND APPARATUS FOR MONITORING ION MASS, ENERGY, AND ANGLE IN PROCESSING SYSTEMS

FIELD

This invention relates to the implantation of workpieces and, more particularly, to a method and apparatus for monitoring ion implantation.

BACKGROUND

Plasma processes are widely used in semiconductor manufacturing, for example, to implant wafers with various dopants, or to deposit or to etch thin films. During a plasma ion implantation process such as plasma doping processes (PLAD), ions are extracted through a high voltage sheath and accelerated toward a target.

In a typical PLAD process, a plasma may be monitored by measuring an implant dose based on a Faraday cup current. However, a Faraday cup is limited to measuring total charge, which does not distinguish between different charged particles or otherwise offer any insight into the plasma. In addition, in pulsed plasma processing wherein a plasma alternates between on and off states, time-resolved measurements of the plasma are often required.

To address some of the above concerns, a time-of-flight ion sensor technique for monitoring ions in a plasma has been developed. In particular, U.S. Pat. No. 7,476,849, issued Jan. 13, 2009, and incorporated by reference herein in its entirety, discloses the use of a time-of-flight sensor to monitor at a fixed angle the plasma species including ions that may impinge on a substrate.

Another method of implanting wafers with various dopants is through the use of ion implantation using a beamline tool. For example, in conventional beamline tools (as well as newly developed ion beam systems based upon plasmas) ions may impinge on a workpiece over a wide range of angles. FIG. 1 is a cross-sectional view of a known focusing plate arrangement for implanting ions having a wide angular distribution on a substrate. The focusing plate **11** is configured to modify an electric field within the plasma sheath **242** to control a shape of a boundary **241** between plasma **14** and the plasma sheath **242**. Accordingly, ions **102** that are attracted from the plasma **14** across the plasma sheath **242** may implant into the workpiece **10** at a large range of incident angles (see, e.g., ion trajectories **269-271**).

In addition to sampling ion species, it may be desirable to measure the angular distribution of ions in such ion beam systems. For example, the exact distribution of ion angles, energies, and mass may be critical in determining the resulting properties of devices formed by such a process. However, none of the aforementioned techniques provide information regarding the mass, ion energy, and angular distribution of ion species.

In view of the above, it will be apparent that in order to achieve predictable and repeatable process results for ion implantation, there is a need to closely monitor and control ion parameters, such as ion energy, angular distribution, and mass.

SUMMARY

In one embodiment, a time-of-flight (TOF) ion sensor system for monitoring an angular distribution of ion species incident on a substrate and having ion energy, comprises a drift tube having a first end configured to receive a pulse of

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ions from the ion species wherein heavier ions and lighter ions of the pulse of ions arrive in packets at a second end of the drift tube, said ion sensor system configured to vary an angle of the drift tube with respect to a plane of the substrate. The ion sensor system may also include an ion detector disposed at the second end of the ion sensor, wherein the ion detector is configured to detect the packets of ions derived from the pulse of ions and corresponding to respective different ion masses.

In another embodiment, a method of measuring ion species incident upon a substrate plane received from a plasma comprises applying a first potential between the plasma and a time-of-flight (TOF) sensor that includes a drift tube and detector, wherein the ion species are attracted to the TOF sensor at a designated ion energy; and performing a first angular scan. The first angular scan includes positioning the TOF sensor in a substrate region at a first angle with respect to the substrate plane and detecting an ion mass of the ion species at the first angle. The first angular scan also includes positioning the time-of-flight sensor at one or more additional angles with respect to the substrate plane and detecting an ion mass of the ion species at the one or more additional angles.

BRIEF DESCRIPTION OF THE DRAWINGS

For a better understanding of the present disclosure, reference is made to the accompanying drawings, which are incorporated herein by reference and in which:

FIG. 1 is a cross-sectional view of a known processing arrangement;

FIGS. 2a and 2b are schematics of a processing system including an exemplary TOF system;

FIG. 3 is a schematic of an exemplary TOF sensor;

FIG. 4 is a schematic of a further exemplary TOF sensor; and

FIG. 5 is a schematic of another exemplary TOF sensor.

DETAILED DESCRIPTION

Embodiments of the invention disclosed herein provide improved processing systems and in particular improved time-of-flight (TOF) ion sensor systems that are suitable for in-situ monitoring and controlling of ion beam and plasma processes, including those that provide ions incident on a substrate over a range of angles. In general, ion energy, mass, and angular distribution may be measured according to the TOF sensor arrangements of the present invention. Each TOF ion sensor may be installed in a variety of ways in a process chamber and may be configured for a number of functions such as, for example, in-situ process control, process readiness verification, fault detection, implant dose correction, and implant uniformity measurement. In particular, the ion mass, energy, and angular distribution may be measured in real time when a substrate is exposed to ions from the plasma, thereby providing a monitoring tool that may be used to develop an implantation profile of a substrate, and/or to adjust plasma parameters in real time to modify the implant profile, among other advantages.

FIG. 2a is a schematic depiction of elements of an exemplary ion processing system (or "processing system") **200** that includes a TOF sensor system, according to an embodiment of this disclosure. Processing system **200** includes a plasma chamber **202** that contains plasma **206**. Coils **204** may be used to create the plasma using RF-induction or may be created by other known methods. In addition, plasma **206** may be created as a continuous or pulsed plasma according to known methods.

Ion processing system **200** may be used to provide ions to a substrate holder **230** for processing a substrate **234**. Such processing may include ion implantation of the substrate or treating patterned surface features such as photoresist structures, among other purposes. A bias may be applied between the plasma and substrate holder in order to cause ions in the plasma to travel towards substrate holder **230** at a desired energy. In one example, a pulsed positive DC-bias **208** may be supplied to plasma **206**, which may serve to accelerate positive ions in the plasma **206** towards substrate holder **230**, which may be at ground potential. Ions that exit the plasma boundary (see element **241** in FIG. 1) and impinge on substrate holder **230** may form a range of angles of incidence. In the embodiment depicted in FIG. 2, a plate **210** is positioned on one side of the plasma chamber **202**, which may provide an ion beam that is extracted through aperture **212** and exhibits a range of ion incidence angles.

Plate (or plasma sheath modifier) **210** may be configured similarly to plate **11** (shown in FIG. 1) in that a plasma sheath shape is modified wherein ions exit the plasma chamber **202** over a range of angles. When ions from plasma **206** impinge on substrate holder **230** their kinetic energy may be determined to a first order by the potential difference between the plasma boundary (**241** in FIG. 1) and substrate **230**, particularly in the case where a collisionless sheath exists between plasma **206** and workpiece **234**. However, it is known that the transfer of energy, momentum, and the implantation range of ions into the substrate, among other processes, may vary substantially among different ions that have the same kinetic energy but have a different angle of incidence toward a substrate.

Processing system **200** also contains a TOF system **220** that may be used to probe ion species, ion energy, and angular distribution for ions extracted from plasma **206**. Moreover, system **200** may provide process monitoring capability, ability to measure ion profile as process parameters are tuned, and ion dose monitoring, among other things.

In accordance with embodiments of this disclosure, system **200** may operate in a variety of modes. In a first mode, system **200** may operate as a "production" tool to provide ions to a workpiece or set of workpieces according to a desired recipe, or set of operating parameters. In this production mode, TOF sensor system **220** does not monitor ions and may be positioned such that it is not exposed to the ions, as depicted in FIG. 2a. Ions extracted from the plasma chamber **202** may enter process chamber **216** and traverse a substrate region **214** of the chamber **216**, in which a substrate holder **230** is typically positioned during the production mode. The ions then impinge upon a substrate **234** and may implant therein according to design. In production mode, the substrate holder **230** may be scanned along the x-direction, for example, to expose an entire substrate **234** to ion bombardment from ions exiting plasma **206** through aperture **212**.

In a replacement mode, depicted in FIG. 2b, TOF sensor system **220** may be deployed within the substrate region **214**, to collect ions in a similar environment as that experienced by the substrate in production mode, while substrate holder **230** is removed from its usual position(s) **230a** used in production mode to allow for more convenient ion measurements.

In a monitoring mode, both substrate holder **230** and TOF sensor system **220** may be simultaneously exposed to ions extracted from plasma **206**, wherein "production" substrates may be implanted and ions collected and analyzed by the TOF sensor at the same time that ion implantation is taking place in the substrate.

An end of sensor **222** that receives ions may be disposed within substrate region **214** and be proximate or at a plane of

workpiece **230** that may represent the plane of workpiece **230** used in production mode. Positioning the sensor **222** in this manner may help to accurately measure the ion profile that is experienced by the workpiece in production mode. In a monitoring mode, both substrate holder **230** and TOF sensor system **220** may be disposed in a position to receive ions extracted from plasma **206**. For example, substrate holder **230** may be configured with an aperture in a middle portion that may be aligned with aperture **212** to provide ions to TOF system **220**. However, other monitoring mode configurations are possible, such as positioning TOF sensor **222** between substrate holder **230** and plate **210**.

In the example of FIGS. 2a, 2b, TOF system **220** includes TOF sensor **222** and TOF sensor positioner (or holder) **224** that may provide a rotational motion and a translational motion in an x- and z-directions, and may also provide motion in a y-direction (coming out of the page). However, other mechanisms are possible for positioning TOF sensor **222**. As used herein the terms "TOF sensor," "TOF ions sensor," and "ion sensor" may be used interchangeably and refer to a device that may contain an extraction electrode, a TOF drift tube and ion detector, among other components. TOF sensor holder **224** may itself be attached to or form a part of chamber **216**. In one example, TOF sensor holder may be configured to attach to a holder or stage, such as substrate holder **230**, or, in another example, may be attached to and controllable by a mechanism located outside chamber **216**.

In accordance with embodiments of the present disclosure, TOF system **220** may provide the capability of measuring ion species and ion energy as a function of angle of incidence. Many components of TOF sensor **222** may be configured according to the configurations disclosed in U.S. Pat. No. 7,476,849. Referring to FIG. 3, there is shown an exemplary ion sensor **100** in accordance with an embodiment of sensor **222**. Ion sensor **100** may comprise a housing **102** that may be adapted for installation in another portion of process chamber **216**, such as a holder **224**. The housing **102** may be individually biased at a desired potential $V_{housing}$. For example, in monitoring or replacement mode, $V_{housing}$ may be set to equal the potential applied to holder **230** in production or monitoring mode, such that ions from plasma **206** are attracted to sensor **222** similarly to the manner in which ions impinge on a substrate **230**.

Ion sensor **100** may also comprise a drift tube **104** inside the housing **102** which may also be individually biased, for example, at a desired potential V_{L3} .

In some embodiments, a pressure surrounding ion sensor **100** may be similar to a plasma chamber's pressure, typically 1-3000 mTorr, while the drift tube is typically operated at 2×10^{-6} Torr or less. Therefore, differential pumping may be provided to accommodate the pressure difference. However, in other embodiments, the pressure surrounding ion sensor **100** may be on the order of 10^{-6} Torr or less, requiring no differential pumping.

Sensor **100** may include an extractor electrode **106** biased at a suitable potential $V_{extractor}$ to attract either positive or negative ions from a plasma, as well as additional lenses **108** and **110**, which may be biased at V_{L1} and lens **110** at V_{L2} , respectively. The drift tube **104**, biased at V_{L3} , may function as a third electrostatic lens in the series. Sensor **100** may be arranged to admit ions in pulses to drift tube **104**, for performing time-of-flight measurements of the ions using detector assembly **112**.

In some embodiments of an ion sensor, an energy analyzer **114** may be provided, as depicted in FIG. 4. One of the electrodes **106-110** may act as a gate, such that when the gate is opened and ions are attracted to drift tube **104**, the ions may

drift into the opposite end of drift tube **104** and into energy analyzer **114**. Energy analyzer **114** may be a known analyzer whose function is to deflect ions toward detector **112** according to a designated ion energy. Accordingly, only ions of the designated energy are deflected to detector **112**.

Thus, after a single gate pulse, detector **112** may detect a series of groups of ions that arrive at detector **112** at different times according to the ion mass, all of which have the ion energy as determined by energy analyzer **114**. A series of measurement may be performed by pulsing the gate and collecting groups of ions at detector **112** after each pulse. According to one embodiment, electrode **110** (i.e., gate electrode) may be normally biased with a positive voltage similar to the plasma potential, except during the very short gating period. For example, a gate pulse width may be about 100 ns.

In a plasma monitoring mode or replacement mode, sensor **100** may be configured to open the gate only near or during periods in which ions are accelerated from a plasma, such as plasma **206**. For example, DC positive voltage pulses **208** may be applied to plasma **206**, wherein workpiece **230** (as well as sensor **100**), which may be grounded, acquires a negative potential with respect to plasma **206**, which may be for example between -10V and -50 kV . Ions are accelerated from the plasma boundary (**241** from FIG. **1**) and may exit aperture **212**, after which the ions may impinge on sensor **100** and workpiece **234** (if workpiece **234** is in place at the time) with an energy determined by the applied DC plasma potential. In some embodiments, gate pulsing to sample ions in the ion sensor may take place only for a small fraction of time, for example, by applying a 100 ns gate pulse for each DC pulse of plasma **206**, which may take place every 200 μs .

In other embodiments, time-resolved measurements may be performed by providing a series of ion sensor gate pulses at various points before, during and/or after the DC pulse is applied. For a DC pulse that lasts on the order of a tenth of a millisecond, many TOF measurements for 100 ns gate pulses may be applied during a single DC plasma pulse as desired.

Referring again to FIG. **2b**, in order to provide information that accurately measures the ion distribution experienced by a workpiece for a given set of operating conditions of system **200**, sensor system **220** may be rotated through a series of angles (see, for example, θ_1 and θ_2) with respect to a plane of substrate **230**, while one or more TOF measurements are performed at each angle. In addition, the position of TOF sensor along the x-direction may be varied and TOF measurements performed as a function of position. For example, referring also to FIG. **1**, system **200** may include an extraction plate similar to extraction plate **11** that is used to provide ions to a workpiece. Holder **224** may be indexed to align sensor **220**, which may be embodied as sensor **100**, with the center of the aperture in plate **11**, as suggested by FIG. **2**. In one example, the aperture is a slit whose width G along the x-direction helps define the width and angular spread of ions on a substrate plane underneath the apertures. Accordingly, a series of TOF measurements at different orientation angles θ may be performed while the extractor side of sensor **100** is near the center **232** of the aperture. In one example, the electrode system of the TOF sensor may provide an acceptance angle of ions on the order of 1 degree or so. It may therefore be convenient to provide a rotation of sensor **100** of at least one degree between each measurement or set of measurements. After performing a series of TOF measurements at discrete angles through a desired angular range, holder **224** may then be scanned with respect to the narrow dimension of the aperture, that is, holder **224** may be moved in a +x or -x direction, after which a further series of measurements through an angular range may be performed.

Accordingly, an exemplary TOF sensor system, such as system **220**, may produce a set of TOF mass spectra that represent the spectra of mass species collected over a set of different angles. Information in the spectra set may include the variation in relative amounts of different ion species (that is, different masses) as a function of angle of incidence.

Additionally, an energy analyzer, such as energy analyzer **114** may be used to collect one or more TOF spectra at one or more ion energies for any desired angle of ion incidence. Because the velocity and therefore time-of-flight of ions in a drift tube is dependent on both ion mass and energy, a detected signal may conflate both ion mass and energy if ions enter the drift tube with a spread of energies and are passed directly to a detector without energy analysis. Accordingly, energy analyzer **114** may be set for a given measurement to deflect only those ions of a designated energy to detector **112**. In this manner, since the energy of detected ions is fixed for a given measurement, all ions of a given mass should arrive at the detector at the same time, thereby ensuring that each peak in a TOF spectrum has a unique mass (or rather mass/charge ratio).

In one example, a 10 keV potential may be applied between the plasma chamber **202** and substrate **230**, while a series of TOF measurements is performed at a fixed angle using different ion energy settings for energy analyzer **114**. The energy of energy analyzer **114** may be initially set at 10 keV to record ions having the nominal ion energy to be investigated. The energy analyzer could subsequently be set to other energies near 10 keV, which may provide useful information concerning the spread of ion energies and ion masses for the given nominal ion energy. Thus, embodiments of the present disclosure may provide a multi-dimensional parameter analysis of energetic ions incident on a substrate, including ion species, energy, and angular of incidence.

Embodiments also enhance the ability to monitor high energy ion processes in a compact environment that may exist in an actual production system. In order to provide a rotatable a TOF sensor that can be conveniently positioned and rotated with a process chamber, it may be desirable to configure the TOF sensor with a relatively short length, thereby requiring a short drift tube design. However, when pulses of ions are admitted toward a drift tube with high ion energies, such as 10 keV or higher, the pulse of ions may arrive at a detector such that ions of different masses are so closely spaced that they cannot be resolved adequately into separate signals or peaks by a detection system. This is because all the high energy ions within a pulse may enter the drift tube with very high velocities in accordance with the ion energy, such that the time-of-flight in the field free region is so short that the difference in time-of-flight duration for ions of differing masses that is too small to resolve in a counter used to detect ions.

In accordance with embodiments of the present disclosure, at least one electrode in a TOF sensor is operable to receive a deceleration potential to counteract the energy of incident ions that enter the TOF sensor before the ions enter the drift tube portion. The magnitude of the deceleration potential may be chosen to reduce the energy of incident ions to a desired level before the ions enter the field-free region whose length dictates the time-of-flight for each ion mass. This may facilitate better mass resolution for TOF measurements of incident ions. Referring to FIG. **3**, a bias may be applied to components of sensor **100** such as electrodes **108**, **110**, drift tube **104**, and detector assembly **112**, in order to reduce the ion energy to a level in which a desired mass resolution can be achieved by sensor **100**.

In one example, a +25 kV retarding potential may be applied to various components of sensor **100** to decelerate

positive ions having 30 keV energy. In one example, electrode **106** may act as a gate electrode, as described above, such that, when the gate is open, 30 keV ions are admitted towards drift tube **104**. The ions may then be decelerated by +25 keV potential applied to electrodes **108**, **110**, **104**, such that a decelerated pulse of ~5 keV ions may then enter drift tube **104**. The time-of-flight difference among 5 keV ions having different mass may then be sufficient for a detector to detect as separate packets thereby producing separate peaks in a mass spectrum.

In one embodiment, the sensor **100** may be operated using a deceleration potential applied to an electrode when the incident ion energy is within a designated range, for example, above 10 keV, while no deceleration potential is applied for ions having lower incident energy. For example, for low energy positive ions, such as 2 keV ions, electrode **108** may be biased at +2 keV under a closed gate mode, and pulsed to -1 keV under an open gate to accelerate ions toward the drift tube, as described above.

In a further embodiment, the TOF sensor, such as sensor **100**, may be configured with an RF bias to help protect the TOF sensor from errors that may be introduced due to exposure to ions over time. In one example, extractor electrode **106** may be provided with a radio frequency (RF) (1-300 MHz, typically 13.56 MHz) bias. The RF biased extractor electrode **106** may serve multiple functions—extracting ions and removing deposits from the extractor aperture—in a deposition-dominant environment. Many manufacturing processes are carried out in a deposition-dominant environment wherein thin-film materials, either electrically conductive or insulating, are deposited in a plasma chamber. If a thick insulating film blocks the extractor aperture, a DC bias on the extractor electrode **106** may no longer be effective. An RF bias may help sputter clean the extractor aperture to remove the deposited materials. That is, an RF bias may provide the ion sensor **300** with a “self-cleaning” capability. For ion extraction, the RF bias may have a negative average potential with respect to the plasma potential. For sputter cleaning purposes, the RF self-bias may be larger than a sputtering threshold and the peak-to-peak value may be 100-1000V or higher. The RF-biased electrode can also act as a capacitive probe to provide information regarding deposition thickness according to known techniques. This information can then be used, for example, to adjust operating parameters of sensor **100**, such as electrode potentials, so that TOF measurements are not affected by accumulation of material around electrodes.

FIG. 5 depicts a further embodiment of an ion sensor. Sensor **500** includes aperture set **502**, which may extract, gate, and/or decelerate ions as described above with respect to ion sensor **100**. Sensor **500** also includes a drift tube **504**, energy analyzer **506**, and detectors **508** and **510**. In some embodiments, sensor **500** may monitor energetic neutrals as well as ions. For example, sensor **500** may be arranged to accept an energetic beam **520**. Sensor **500** may be arranged to collect such a beam over a range of angles as described above with respect to sensor system **220**. Energetic beam **520** may comprise energetic ions that are accelerated to a desired ion energy and energetic neutrals that result from the ions that are neutralized after extraction and/or deceleration. The energetic neutrals may typically have energies similar to the desired ion energy or less than the desired ion energy. When beam **520** passes through drift tube **504**, ions and neutrals may travel together through the drift tube. When ions **512** pass through energy analyzer **506**, they may be deflected as shown and be detected by detector **508** disposed in a side portion of the ion sensor **500**. The energy analyzer **506** may be

a magnetic analyzer for example that creates a B-field to deflect electrically charged species, for example, positive ions, in the direction shown. However, because the energetic neutrals **514** do not carry charge, the energetic neutrals **514** may continue in a straight trajectory as shown, to be detected by “in-line” detector **508**. Accordingly, ion sensor **500** may be used to provide information concerning the amount of energetic neutrals and their angular distribution, as well as information regarding energetic ions similar to that provided by the aforementioned embodiments depicted in FIGS. 1-4.

It should be noted that the ion sensor systems in accordance with the present disclosure as described above typically involve the processing of input data and the generation of output data to some extent. This input data processing and output data generation may be implemented in hardware or software. For example, specific electronic components may be employed in an ion beam processing tool or similar or related circuitry for implementing the functions associated with in-situ monitoring of ion species in accordance with the present disclosure as described above. Alternatively, one or more processors operating in accordance with stored instructions may implement the functions associated with in-situ monitoring of ion species in accordance with the present disclosure as described above. If such is the case, it is within the scope of the present disclosure that such instructions may be stored on one or more processor readable carriers (e.g., a magnetic disk), or transmitted to one or more processors via one or more signals.

The present disclosure is not to be limited in scope by the specific embodiments described herein. Indeed, other various embodiments of and modifications to the present disclosure, in addition to those described herein, will be apparent to those of ordinary skill in the art from the foregoing description and accompanying drawings. For example, although embodiments of the disclosure have been depicted in which an ion beam system employs an extraction plate to form an ion beam, the TOF sensor system of the present invention may be advantageously deployed in many types of apparatus that generate ions including those without such extraction plates. Moreover, the TOF sensor system can operate in a processing system in which only a monitoring mode or only a replacement mode is practical.

Thus, such other embodiments and modifications are intended to fall within the scope of the present disclosure. Furthermore, although the present disclosure has been described herein in the context of a particular implementation in a particular environment for a particular purpose, those of ordinary skill in the art will recognize that its usefulness is not limited thereto and that the present disclosure may be beneficially implemented in any number of environments for any number of purposes. Thus, the claims set forth below should be construed in view of the full breadth and spirit of the present disclosure as described herein.

What is claimed is:

1. A method of measuring ion species incident upon a substrate plane received from a plasma comprising:
 - generating the plasma in a plasma chamber, the plasma chamber comprising a plasma sheath modifier and an aperture defined in the plasma sheath modifier, the aperture having a width along a first direction;
 - applying a first potential between the plasma and a time-of-flight (TOF) sensor, the TOF sensor comprising a drift tube having a first end configured to receive ion species generated in the plasma chamber and a detector disposed at a second end of the drift tube;
 - attracting the ion species to the detector of the TOF sensor at a designated ion energy;

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performing a series of TOF measurements of ions by rotating the drift tube through a first angular range; moving the TOF sensor along the first direction; and performing a further series of TOF measurements of ions by rotating the drift tube through a second angular range.

2. The method of claim 1, further comprising:
 providing an RF bias voltage to an electrode of the TOF sensor that acts as a capacitive probe;
 monitoring a deposition thickness of material accumulated on the electrode; and
 adjusting operating parameters of the TOF sensor in accordance with the deposition thickness.

3. The method of claim 1, further comprising:
 providing an energy analyzer between the drift tube and the detector; and
 setting the energy analyzer to transmit to the detector ions received from the drift tube according to a desired energy.

4. The method of claim 1, wherein the ion species are positive ions, the step of detecting the ion mass further comprising:
 providing a pulse of voltage on a first electrode in the TOF sensor that is negative with respect to a plasma voltage; and
 recording a time-of-flight of ion species through the drift tube at the detector.

5. The method of claim 4, further comprising providing a deceleration potential on a second electrode that decelerates the ions below the designated energy before the ions enter the drift tube.

6. The method of claim 5, wherein the first electrode comprises a gate electrode that is configured to block ions entering the TOF sensor in a closed mode and is configured to transmit ions toward the drift tube during an open mode corresponding to a duration of the voltage pulse on the first electrode.

7. The method of claim 6, wherein the first potential is applied as a series of DC pulses, wherein the open mode is triggered one or more times during the voltage pulse.

8. An ion implantation system, comprising:
 a plasma source configured to generate a plasma at a plasma potential in a plasma chamber, the plasma source comprising a plasma sheath modifier and an aperture defined in the plasma sheath modifier, the aperture having a width in a first direction;
 a substrate holder operable to position a substrate in a substrate plane of a substrate region and to receive a substrate potential, wherein the plasma chamber supplies an ion beam into the substrate region containing ions incident over a range of angles at an energy defined by a difference in a potential of the plasma and a potential of the substrate; and
 a time-of-flight (TOF) ion sensor system disposed near the substrate holder, said TOF ion sensor system including:

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a TOF sensor comprising a drift tube having a first end operable to receive the ions in the substrate region generated by the plasma chamber and configured to receive the substrate potential, the TOF sensor including a detector disposed at a second end of the drift tube; and
 a positioner configured to vary an angle of the TOF sensor by rotating the drift tube through a first angular range with respect to the substrate plane in a first series of TOF measurements, move the TOF sensor along the first direction and conduct a second series of TOF measurements of ions by rotating the drift tube through a second angular range.

9. The ion implantation system of claim 8, wherein the plasma sheath modifier is configured to provide ions to the substrate plane over the range of angles.

10. The method of claim 1, wherein the first angular range and the second angular range are the same.

11. The ion implantation system of claim 8, wherein the first angular range and the second angular range are the same.

12. The method of claim 1, wherein the first direction is orthogonal to a second direction, the method further comprising moving the detector in a third direction orthogonal to the first and second directions such that the detector remains at a set position with respect to the first direction.

13. The ion implantation system of claim 8, wherein the first direction is orthogonal to a second direction, and the positioner is further configured to move the detector in a third direction orthogonal to the first and second directions such that the detector remains at a set position with respect to the first direction.

14. A method of measuring ion species incident upon a substrate plane received from a plasma comprising:
 generating the plasma in a plasma chamber, the plasma chamber comprising a plasma sheath modifier and an aperture defined in the plasma sheath modifier, the aperture having a width along a first direction;
 applying a first potential between the plasma and a time-of-flight (TOF) sensor, the TOF sensor comprising a drift tube extending in a second direction orthogonal to the first direction, a first end configured to receive ion species generated in the plasma chamber and a detector disposed at a second end of the drift tube;
 attracting the ion species to the detector of the TOF sensor at a designated ion energy;
 performing a series of TOF measurements of ions by rotating the drift tube through a first angular range;
 moving the detector in a third direction orthogonal to the first and second directions such that the detector remains at a set position with respect to the first direction;
 moving the TOF sensor along the first direction; and
 performing a further series of TOF measurements of ions by rotating the drift tube through second angular range.

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